

N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^d	Q _g (Typ.)
100	0.124 at V _{GS} = 10 V	4.2	4.6 nC
	0.128 at V _{GS} = 4.5 V	3.9	

FEATURES

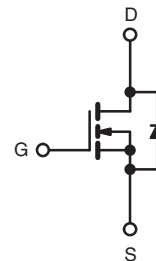
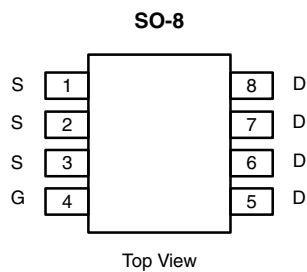
- TrenchFET[®] Power MOSFET
- 100 % UIS Tested

APPLICATIONS

- High Frequency Boost Converter
- LED Backlight for LCD TV



RoHS
COMPLIANT
HALOGEN
FREE



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	100	V	
Gate-Source Voltage	V _{GS}	± 20		
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	4.2	A
		T _C = 70 °C	3.5	
		T _A = 25 °C	3.0 ^{a, b}	
		T _A = 70 °C	2.4 ^{a, b}	
Pulsed Drain Current	I _{DM}	16		
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	4.0	
		T _A = 25 °C	2 ^{a, b}	
Single Avalanche Current	I _{AS}	6	A	
Single Avalanche Energy	E _{AS}	1.8	mJ	
Maximum Power Dissipation	P _D	T _C = 25 °C	4.8	W
		T _C = 70 °C	3	
		T _A = 25 °C	2.4 ^{a, b}	
		T _A = 70 °C	1.5 ^{a, b}	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{a, c}	R _{thJA}	42	53	°C/W
Maximum Junction-to-Foot (Drain)	R _{thJF}	21	26	

Notes:

- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under steady state conditions is 85 °C/W.
- Based on T_C = 25 °C.

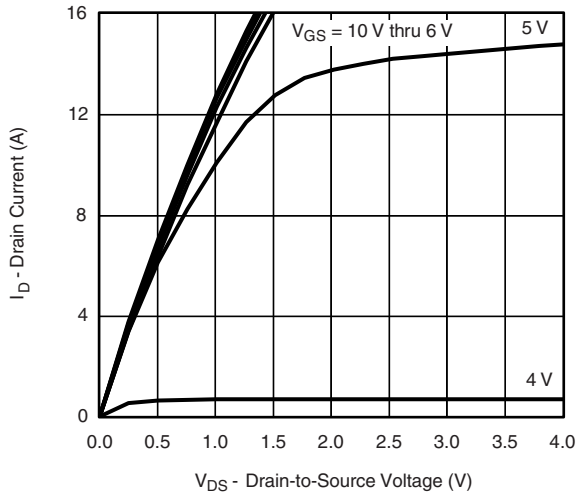
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	100			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		110		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			-7.5		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1		3	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	8			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 2.7\text{ A}$		0.124	0.150	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 2.5\text{ A}$		0.128	0.155	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 10\text{ V}, I_D = 2.7\text{ A}$		7		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		470		pF
Output Capacitance	C_{oss}			50		
Reverse Transfer Capacitance	C_{rss}			25		
Total Gate Charge	Q_g	$V_{DS} = 50\text{ V}, V_{GS} = 10\text{ V}, I_D = 2.7\text{ A}$		7.1	11	nC
				4.6	7	
Gate-Source Charge	Q_{gs}	$V_{DS} = 50\text{ V}, V_{GS} = 6\text{ V}, I_D = 2.7\text{ A}$		1.7		
Gate-Drain Charge	Q_{gd}			2		
Gate Resistance	R_g	$f = 1\text{ MHz}$		3		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 50\text{ V}, R_L = 23.8\text{ }\Omega$ $I_D \cong 2.1\text{ A}, V_{GEN} = 6\text{ V}, R_g = 1\text{ }\Omega$		10	15	ns
Rise Time	t_r			10	15	
Turn-Off Delay Time	$t_{d(off)}$			10	15	
Fall Time	t_f			10	15	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 50\text{ V}, R_L = 23.8\text{ }\Omega$ $I_D \cong 2.1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		10	15	
Rise Time	t_r			10	15	
Turn-Off Delay Time	$t_{d(off)}$			12	20	
Fall Time	t_f			10	15	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			4	A
Pulse Diode Forward Current	I_{SM}				8	
Body Diode Voltage	V_{SD}	$I_S = 2.1\text{ A}, V_{GS} = 0\text{ V}$		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 2.1\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		50	80	ns
Body Diode Reverse Recovery Charge	Q_{rr}			75	120	nC
Reverse Recovery Fall Time	t_a			28		ns
Reverse Recovery Rise Time	t_b			22		

Notes:

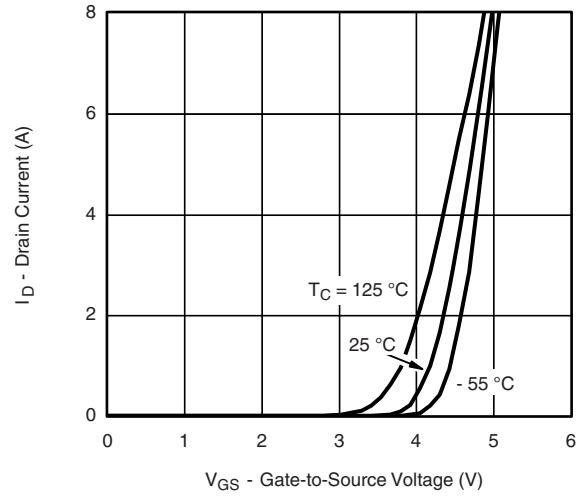
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

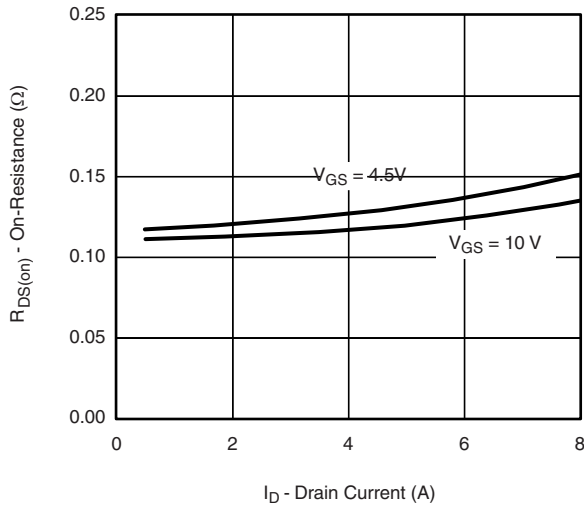
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



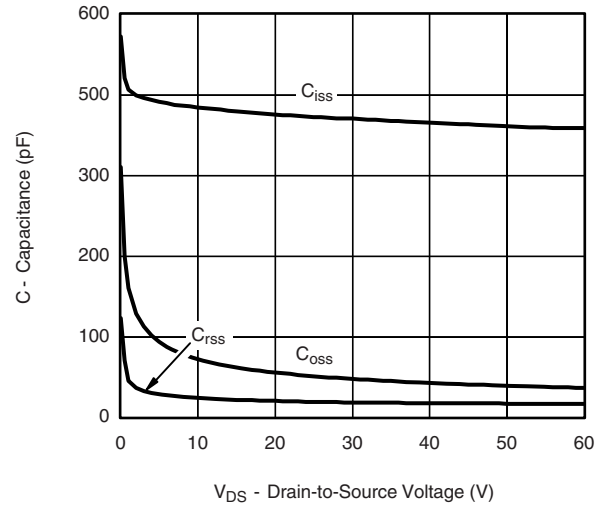
Output Characteristics



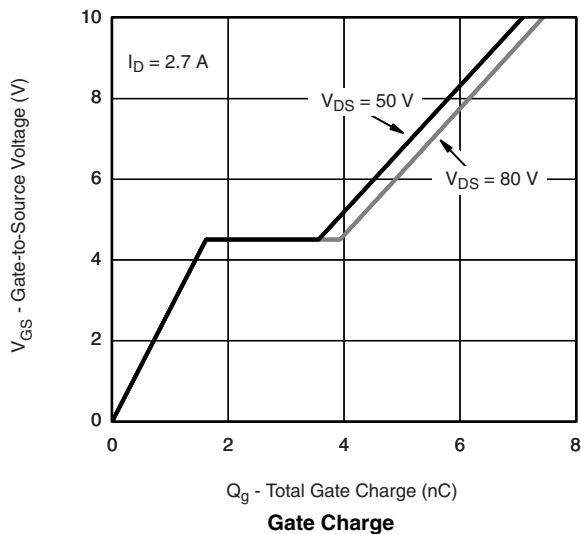
Transfer Characteristics



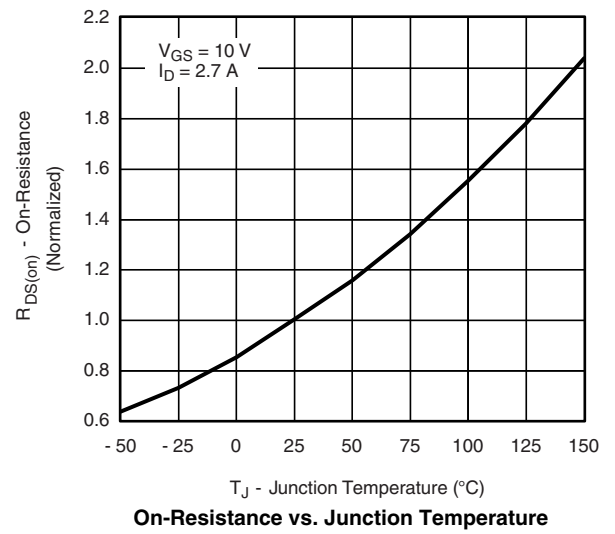
On-Resistance vs. Drain Current



Capacitance

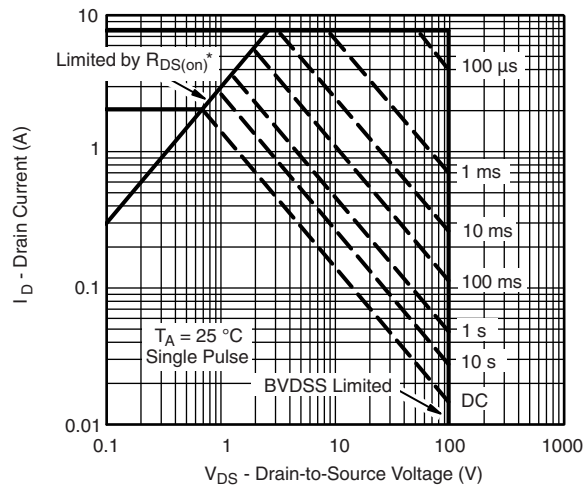
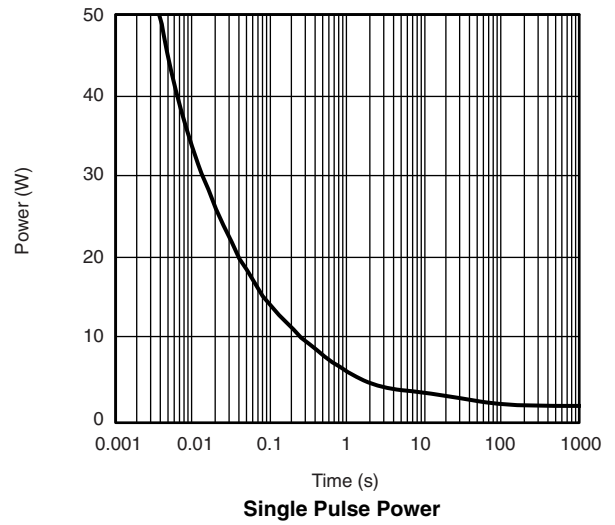
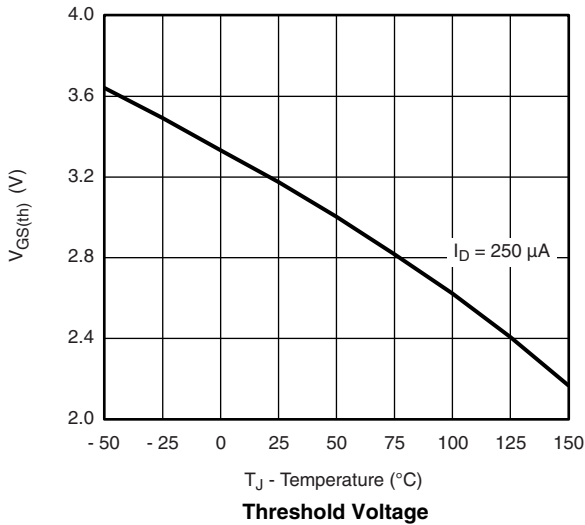
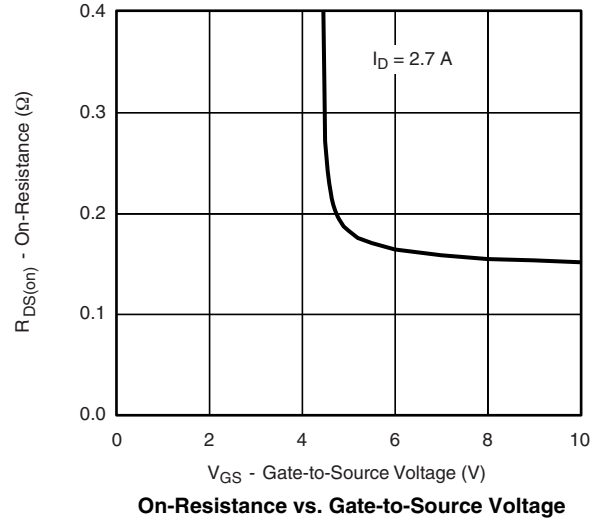
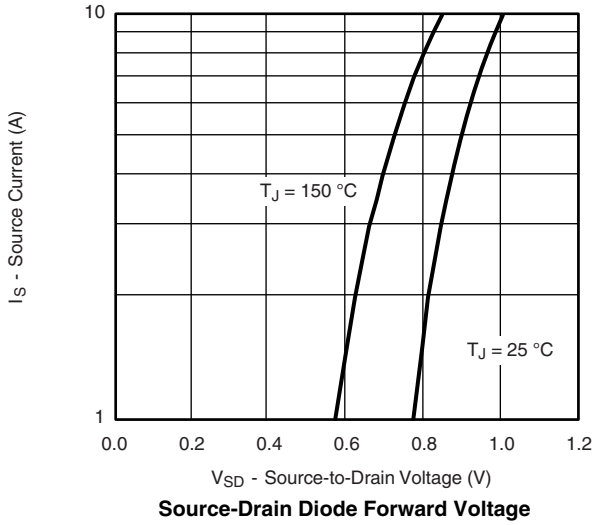


Gate Charge



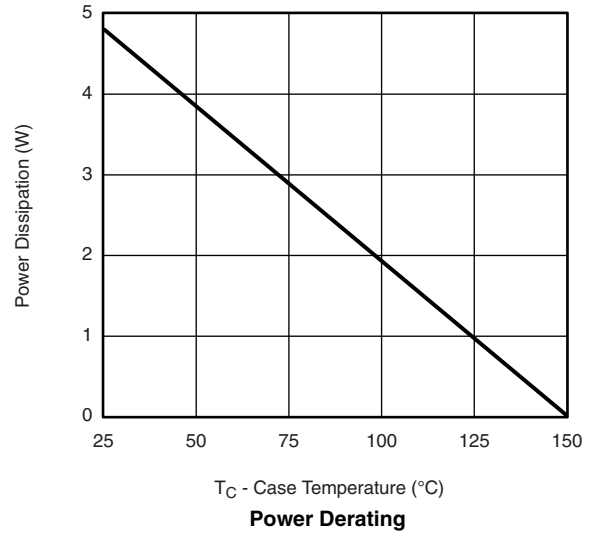
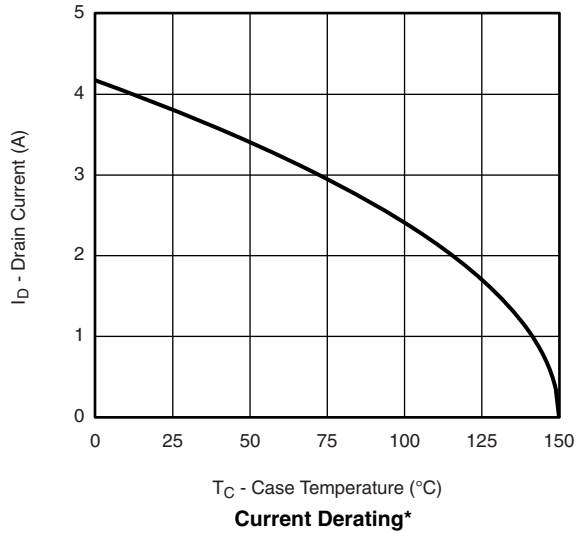
On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



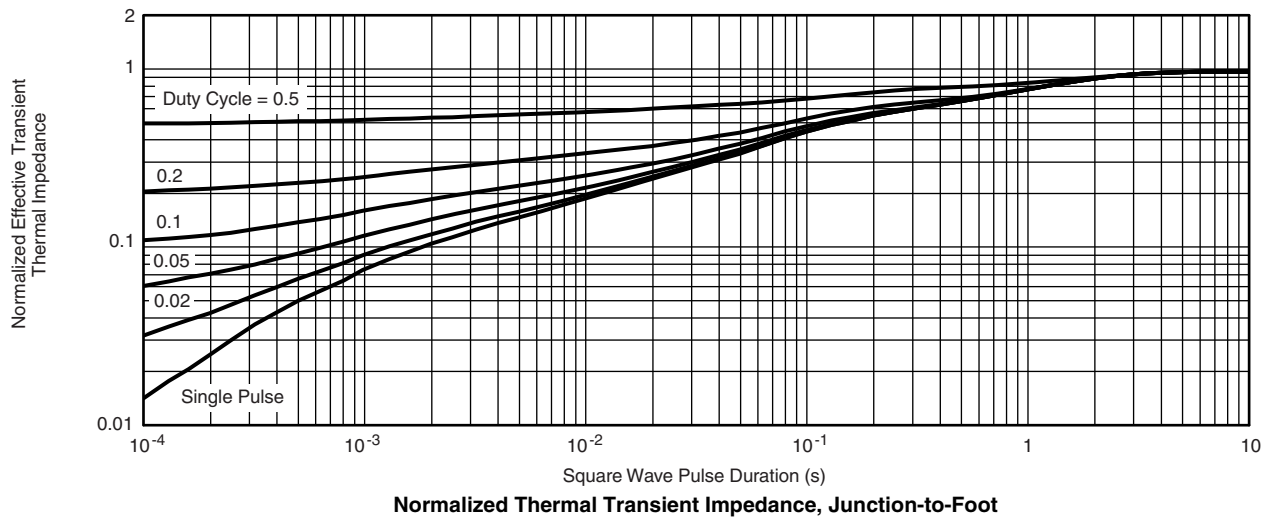
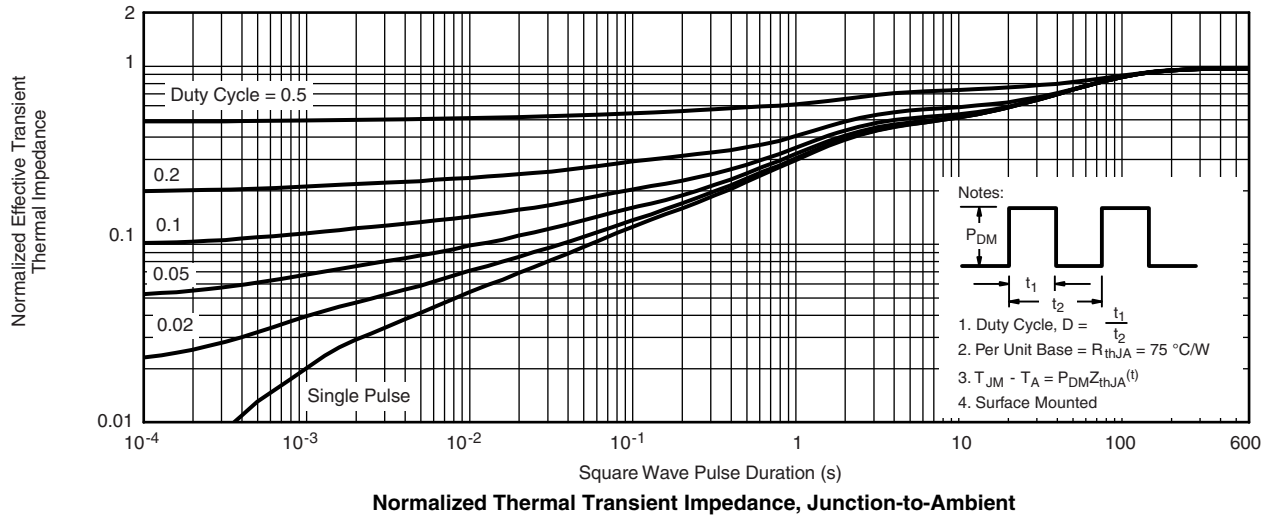
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

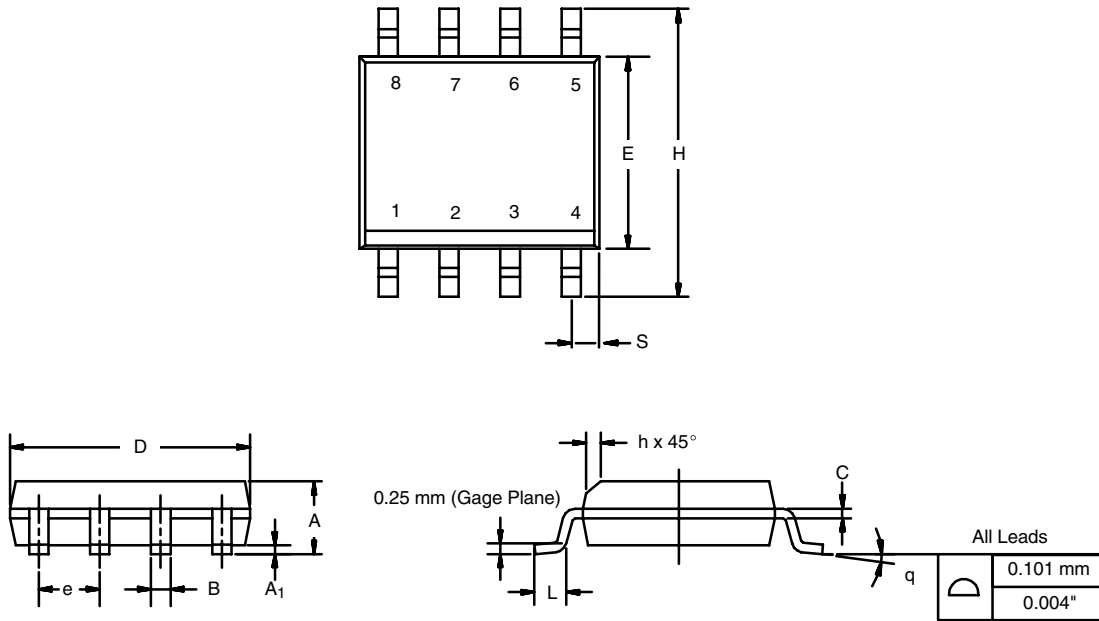


* The power dissipation P_D is based on $T_{J(max.)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

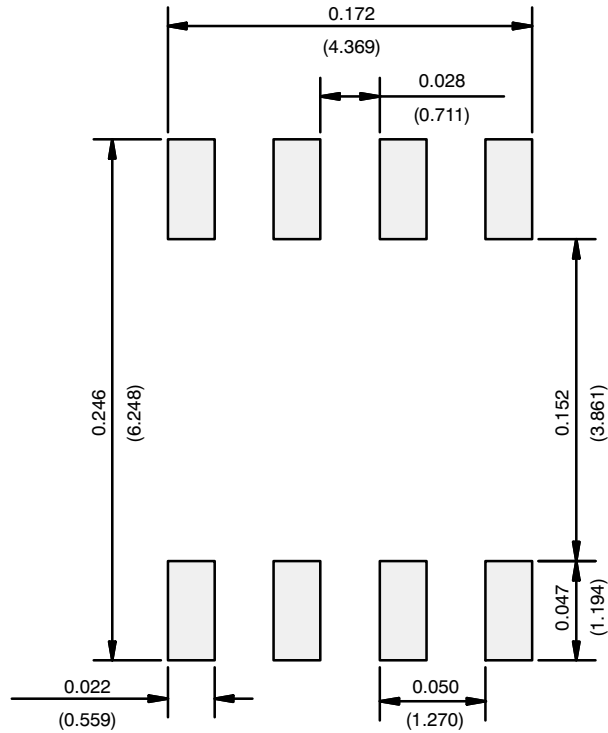


SOIC (NARROW): 8-LEAD
JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

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